

Search History (7 pp.) *He* (7/26/05)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	28	(US-20020074601-\$ or US-20020135067-\$ or US-20020137301-\$ or US-20020195633-\$ or US-20030211685-\$ or US-20040238862-\$).did. or (US-6072689-\$ or US-6090443-\$ or US-6146963-\$ or US-6236113-\$ or US-6399521-\$ or US-6479304-\$ or US-6566753-\$ or US-6611014-\$ or US-6613640-\$).did. or (EP-1035589-\$ or EP-1054440-\$ or EP-821415-\$).did. or (JP-2001036026-\$ or JP-2001118941-\$ or JP-2003273323-\$).did. or (EP-905786-\$ or JP-2001036026-\$ or DE-10105997-\$ or US-20040004236-\$ or US-20040129670-\$ or US-20040180453-\$ or US-20040195613-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/26 10:41
L2	4	L1 and resist near4 etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 11:01
L3	2	("20020074601").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:01
L4	2	1 and hard adj mask near10 etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:01
L5	2536	438/3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:29
L6	2337	438/197	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:29

L7	2477	438/238	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:29
L8	155467	"438"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:29
L9	7777	((438/239) or (438/240) or (438/253) or (438/254) or (438/706) or (438/734) or (438/3) or (438/197)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/07/26 12:31
L10	65	9 and (feRAM ferroelectric).ti,ab, clm. and semiconductor and etch\$3 and hard adj mask and resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 12:32
S1	3	"743073".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 08:33
S2	180	(257/254).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 08:58
S3	925	(257/734).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 08:58
S4	0	S2 and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 08:58
S5	570	(438/254).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 08:59
S6	429	(438/734).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 08:59
S7	3	S5 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:05
S8	1547	(438/3).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:05
S9	1039	(438/197).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:05
S10	1060	(438/238).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:05

S11	907	(438/239).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:05
S12	1232	(438/240).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:05
S13	2192	(438/253).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:06
S14	1054	(438/706).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:06
S15	7846	S5 S6 S8 S9 S10 S11 S12 S13 S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:28
S16	2688	S15 and (etching etchant etch) and (annealing anneal heat adj (treatment treating treated))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:14
S17	123	S16 and capacitor and second near3 (etching etch) near3 step	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:13
S18	0	S17 and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:14
S19	97	S16 and capacitor and second near3 (etching etch) near3 step and (anneal annealing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:13
S20	35	S17 and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:10
S21	6	S17 and ferroelectric and adhesion adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:12
S22	1	S17 and ferroelectric and adhesion adj layer near4 (etch etching etchant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:12

S23	742	S15 and (etching etchant etch) and (annealing anneal heat adj (treatment treating treated)) and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:14
S24	18	S15 and (etching etchant etch) and (annealing anneal heat adj (treatment treating treated)) and ferroelectric and (adhesion adhesive buffer) near2 (etch etching etchant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 11:13
S25	2	jp-2001036026\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 11:16
S26	3	("6611014").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:17
S27	7	(US-20040238862-\$ or US-20020195633-\$ or US-20030211685-\$ or US-20020074601-\$).did. or (US-6611014-\$).did. or (JP-2001036026-\$).did. or (JP-2001036026-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/02/28 15:31
S28	5	barrier and S27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 15:58
S29	35	oxygen adj barrier near6 lower adj electrode and capacitor and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 15:58
S30	7	(US-20020074601-\$ or US-20020195633-\$ or US-20030211685-\$ or US-20040238862-\$).did. or (US-6611014-\$).did. or (JP-2001036026-\$).did. or (JP-2001036026-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/01 06:59
S31	5	S30 and (Ir IrO iridium iridium adj oxide "Ir.sub."\$3"O")	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/01 08:09

S32	2	("6090443").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/01 08:14
S33	0	("oxygenadjdiffusionandferroelectr icadjcapacitor").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/01 08:14
S34	171	oxygen adj diffusion and ferroelectric adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/01 08:15
S35	41	oxygen adj diffusion.ti,ab,clm. and ferroelectric adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/01 08:15
S36	27	oxygen adj diffusion.ti,ab,clm. and ferroelectric adj capacitor.ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/01 08:15
S37	28	(US-20020074601-\$ or US-20020195633-\$ or US-20030211685-\$ or US-20040238862-\$ or US-20020137301-\$ or US-20020135067-\$).did. or (US-6611014-\$ or US-6090443-\$ or US-6613640-\$ or US-6566753-\$ or US-6479304-\$ or US-6399521-\$ or US-6236113-\$ or US-6146963-\$ or US-6072689-\$).did. or (EP-1054440-\$ or EP-1035589-\$ or EP-821415-\$).did. or (JP-2001036026-\$ or JP-2003273323-\$ or JP-2001118941-\$).did. or (JP-2001036026-\$ or US-20040195613-\$ or US-20040180453-\$ or US-20040129670-\$ or US-20040004236-\$ or DE-10105997-\$ or EP-905786-\$). did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/01 08:32

S38	28	(US-20020074601-\$ or US-20020195633-\$ or US-20030211685-\$ or US-20040238862-\$ or US-20020137301-\$ or US-20020135067-\$).did. or (US-6611014-\$ or US-6090443-\$ or US-6613640-\$ or US-6566753-\$ or US-6479304-\$ or US-6399521-\$ or US-6236113-\$ or US-6146963-\$ or US-6072689-\$).did. or (EP-1054440-\$ or EP-1035589-\$ or EP-821415-\$).did. or (JP-2001036026-\$ or JP-2003273323-\$ or JP-2001118941-\$).did. or (JP-2001036026-\$ or US-20040195613-\$ or US-20040180453-\$ or US-20040129670-\$ or US-20040004236-\$ or DE-10105997-\$ or EP-905786-\$). did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/01 09:00
S39	28	S38 and ferroelectric and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/01 09:01
S40	2	("20020074601").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/25 14:53
S41	529	titanium adj oxide near4 insulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/25 15:34
S42	1266	((sputter\$3 deposit\$3) near3 (passivati\$2 encapsulati\$2)) same (etch\$3 near3 (passivati\$2 encapsulati\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:36
S43	36	((sputter\$3 deposit\$3) near3 (passivati\$2 encapsulati\$2)) same (etch\$3 near3 (passivati\$2 encapsulati\$2)) and ferroelectric. ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:38
S44	16	((sputter\$3 deposit\$3) near3 (passivati\$2 encapsulati\$2)) same (etch\$3 near3 (passivati\$2 encapsulati\$2)) and ferroelectric. ti,ab,clm. and ("257"/\$7.ccls. "438"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:41

S45	4	((sputter\$3 deposit\$3) near3 (passivati\$2 encapsulati\$2)) same (etch\$3 near3 (passivati\$2 encapsulati\$2)) near6 ((lower bottom) near2 electrode) and ferroelectric.ti,ab,clm. and ("257"/\$7.ccls. "438"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 16:00
S46	0	(etch\$3 near3 (passivati\$2 encapsulati\$2)) near6 ((lower bottom) near2 electrode near8 self-align\$4) and ferroelectric.ti,ab,clm. and ("257"/\$7.ccls. "438"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 16:02
S47	7	(etch\$3 near5 (self-align\$4 selfalign\$4)) near5 ((bottom lower) adj electrode) and ferroelectric.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 16:03
S48	3	self-align\$4 near6 bottom adj electrode near6 etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 08:36
S49	14	self-align\$4 near6 (lower bottom) adj electrode near6 etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 08:37